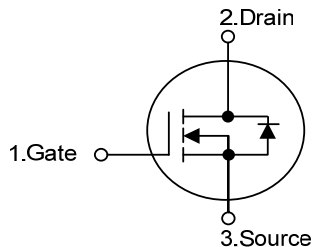


**8N65****Power MOSFET****8A, 650V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **8N65** is a high voltage and high current power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

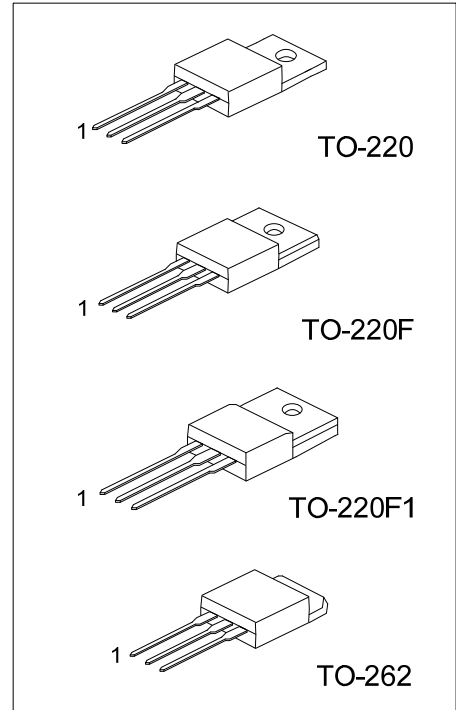
- * $R_{DS(ON)} = 1.4\Omega @ V_{GS} = 10V$
- * Ultra low gate charge (typical 28 nC)
- * Low reverse transfer capacitance (C_{RSS} = typical 12.0 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N65L-TA3-T	8N65G-TA3-T	TO-220	G	D	S	Tube
8N65L-TF1-T	8N65G-TF1-T	TO-220F1	G	D	S	Tube
8N65L-TF3-T	8N65G-TF3-T	TO-220F	G	D	S	Tube
8N65L-T2Q-T	8N65G-T2Q-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

8N65L-TA3-T (1) Packing Type (2) Package Type (3) Lead Free	(1) T: Tube (2) TA3: TO-220, TF1: TO220-F1, TF3: TO-220F T2Q: TO-262 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	8	A
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	230	mJ
	Repetitive (Note 2)	E_{AR}	14.7	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262	P_D	147	W
	TO-220F/TO-220F1		48	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 7.1\text{mH}$, $I_{AS} = 8\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 8\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262	θ_{JC}	0.85	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.6	$^\circ\text{C}/\text{W}$

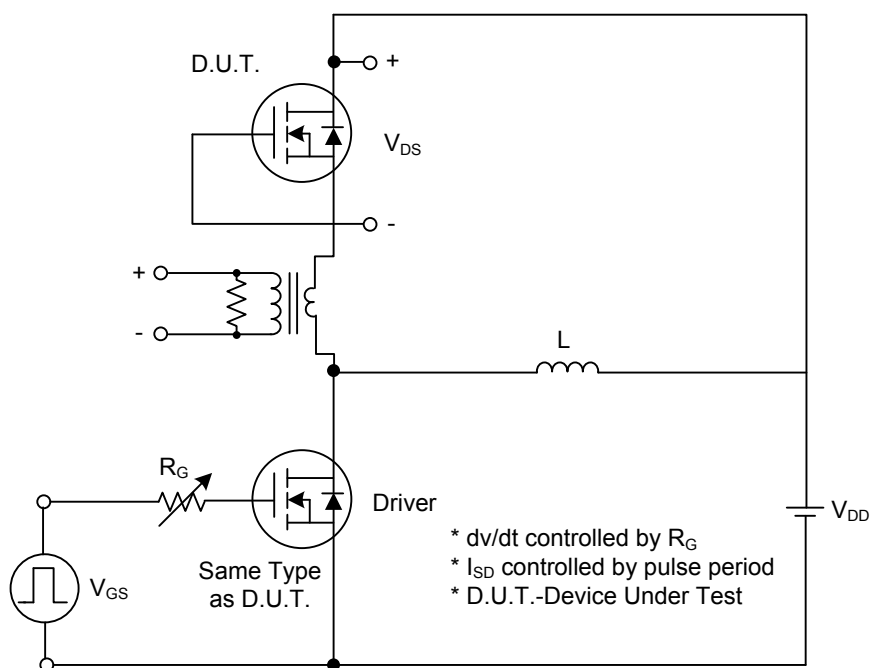
■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0 V, I _D = 250 μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
	Reverse		V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA,Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10 V, I _D = 4A		1.0	1.4	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} = 25 V, V _{GS} = 0V, f = 1MHz		965	1255	pF
Output Capacitance		C _{OSS}			105	135	pF
Reverse Transfer Capacitance		C _{RSS}			12	16	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	V _{DD} = 325V, I _D =8A, R _G = 25Ω (Note 1, 2)		16.5	45	ns
Turn-On Rise Time		t _R			60.5	130	ns
Turn-Off Delay Time		t _{D(OFF)}			81	170	ns
Turn-Off Fall Time		t _F			64.5	140	ns
Total Gate Charge		Q _G	V _{DS} = 520V,I _D =8A, V _{GS} = 10 V (Note 1, 2)		28	36	nC
Gate-Source Charge		Q _{GS}			4.5		nC
Gate-Drain Charge		Q _{GD}			12		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} = 0 V, I _S =8A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				8	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				32	A
Reverse Recovery Time		t _{RR}	V _{GS} = 0 V, I _S =8A,		365		ns
Reverse Recovery Charge		Q _{RR}	dl _F /dt = 100 A/μs (Note 2)		3.4		μC

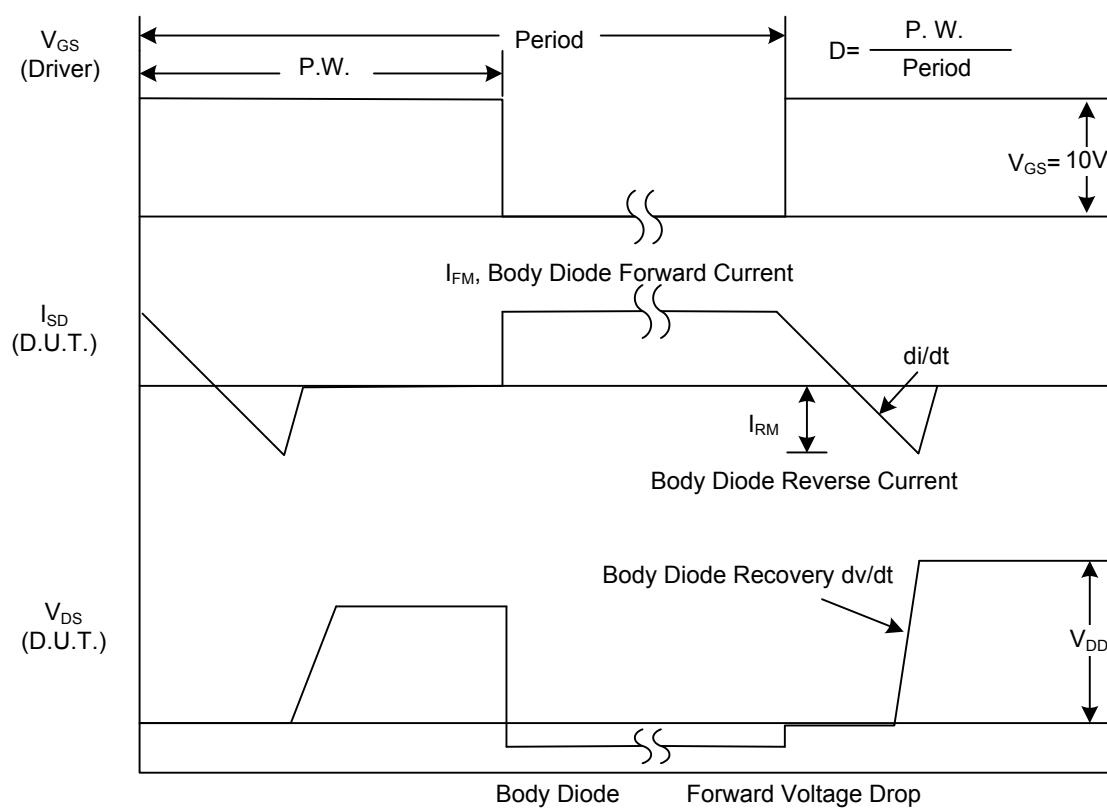
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

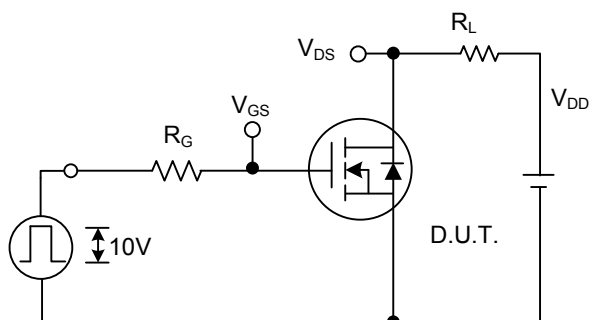


Peak Diode Recovery dv/dt Test Circuit

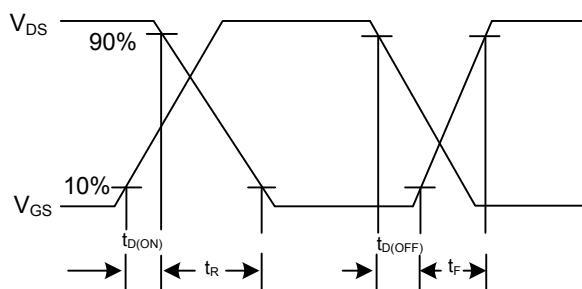


Peak Diode Recovery dv/dt Waveforms

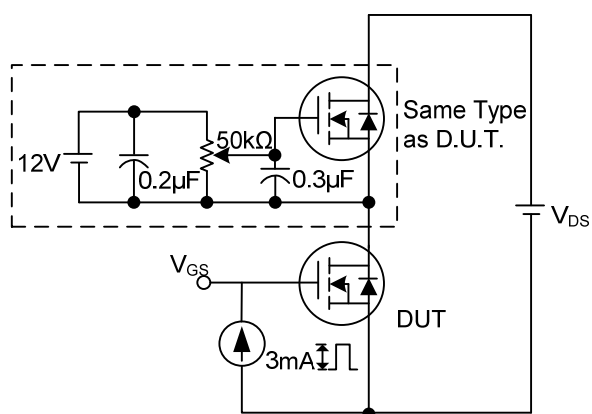
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



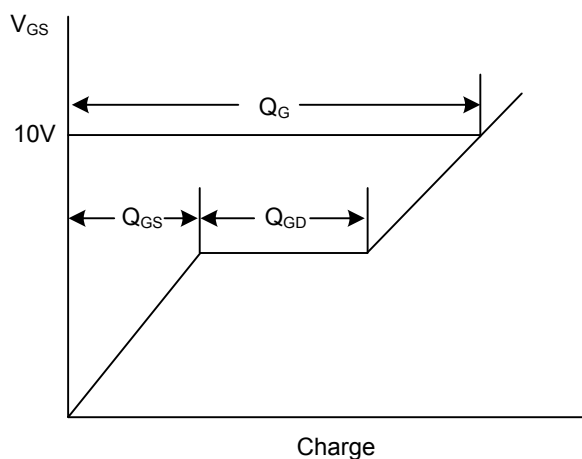
Switching Test Circuit



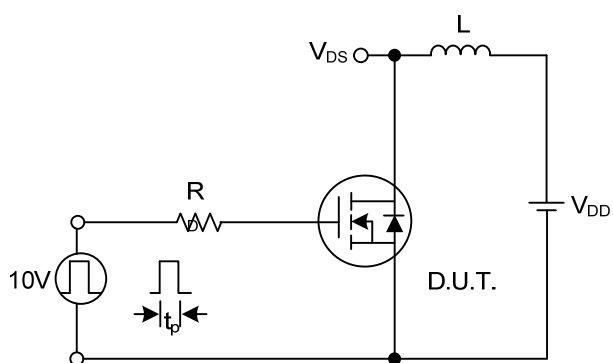
Switching Waveforms



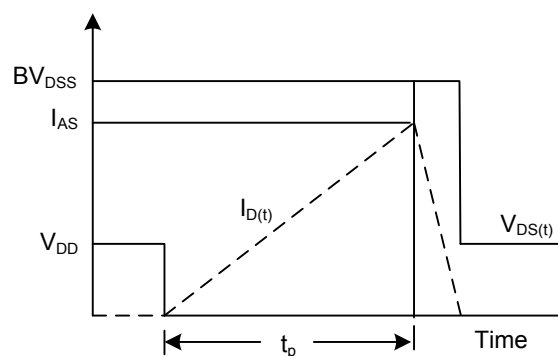
Gate Charge Test Circuit



Gate Charge Waveform

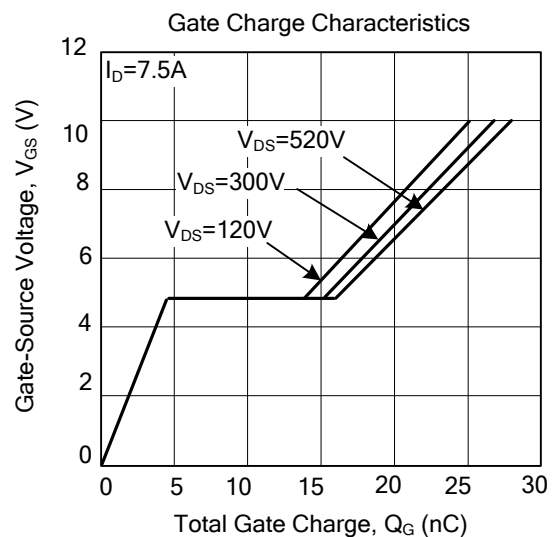
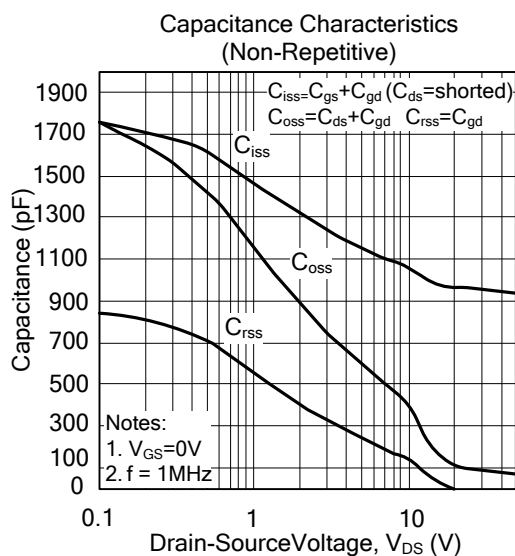
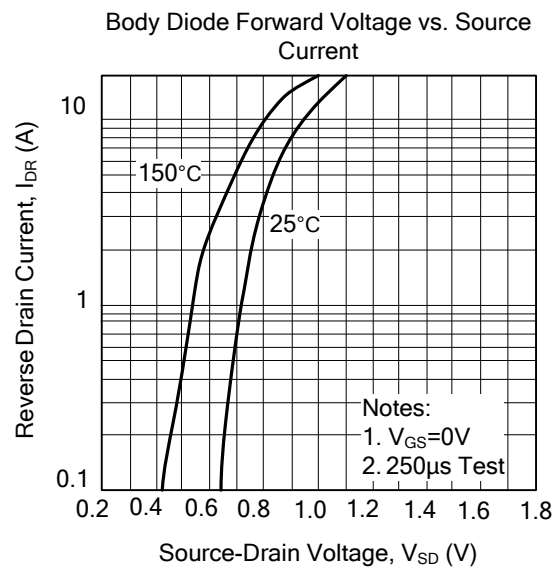
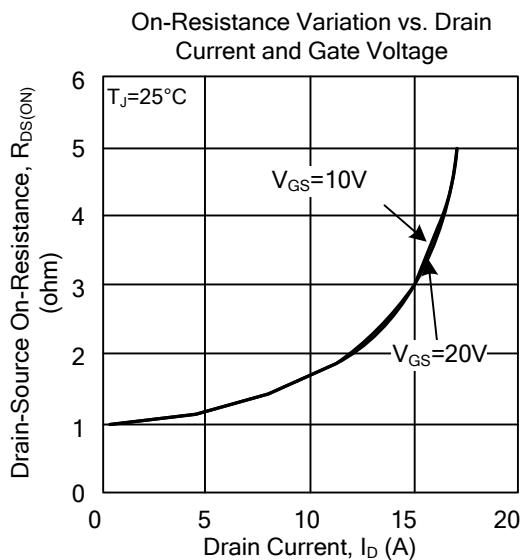
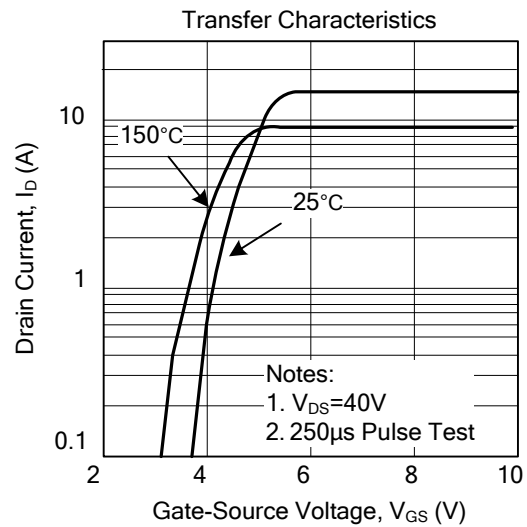
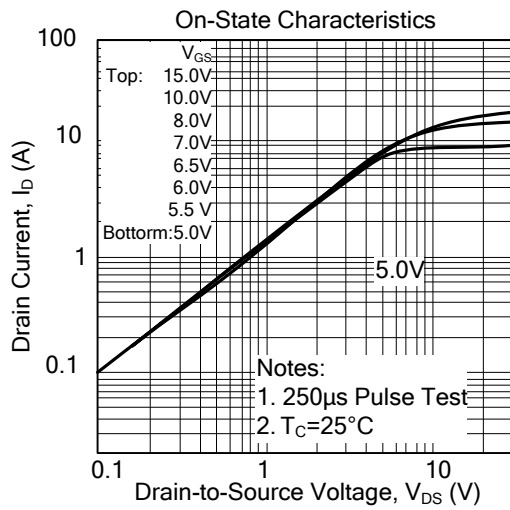


Unclamped Inductive Switching Test Circuit

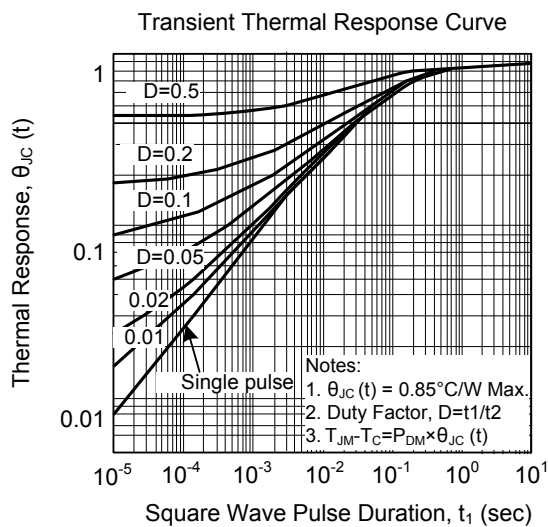
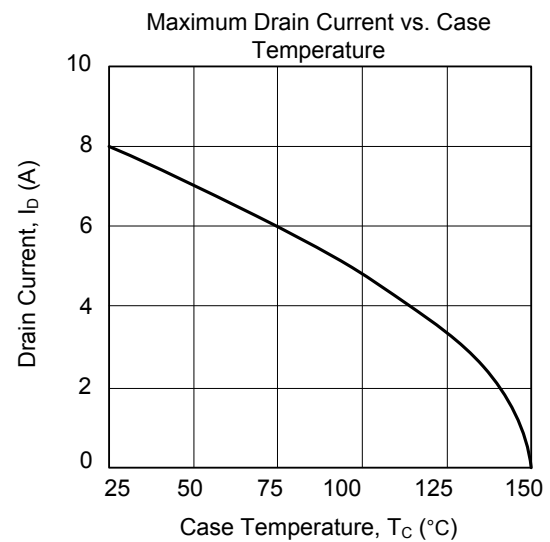
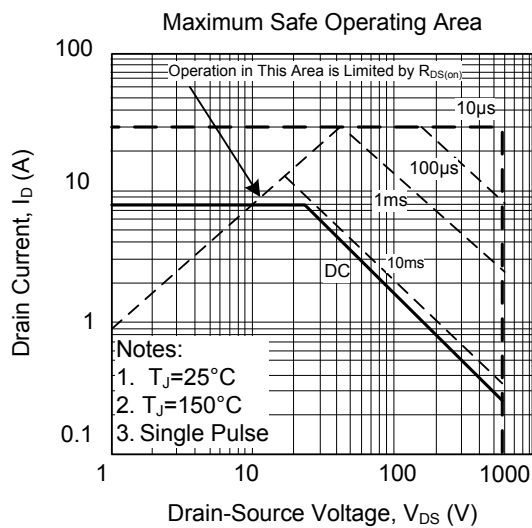
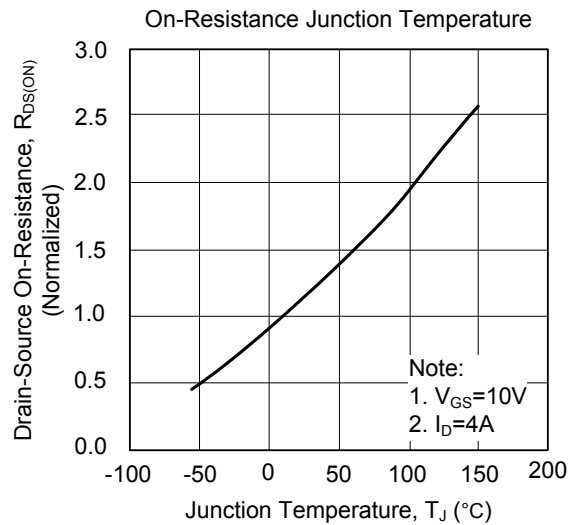
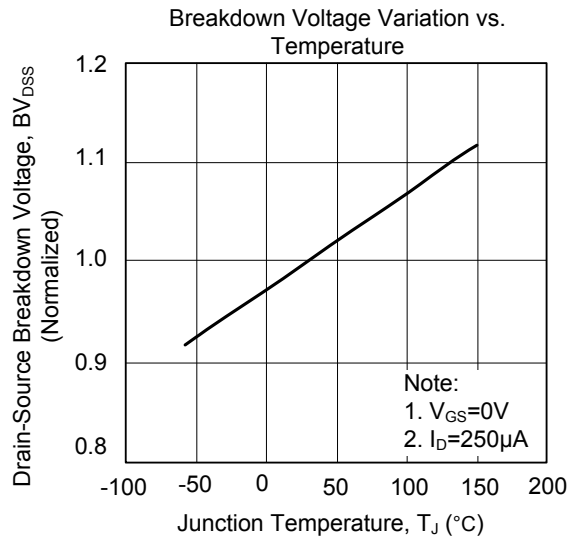


Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS(Cont.)



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